

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-60V	110mΩ @ V <sub>GS</sub> = -10V	-4.2A
	130mΩ @ V <sub>GS</sub> = -4.5V	-3.9A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

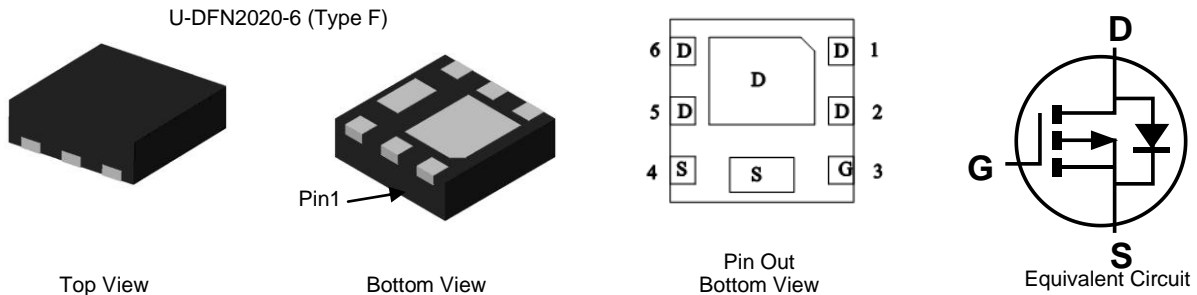
- Battery Management Application
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- 100% Unclamped Inductive Switching Test in Production – Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Notes 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>e4</sup>
- Weight: 0.007 grams (Approximate)

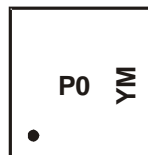


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP6110SFDFQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP6110SFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
  5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



P0 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: G = 2019)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	F	G	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-3.5 -2.8	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-4.2 -3.4	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-20	A
Continuous Source-Drain Diode Current (Note 7)		T <sub>A</sub> = +25°C	I <sub>S</sub>	-2.1	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-20	A
Avalanche Current (Note 8) L = 0.1mH			I <sub>AS</sub>	-19	A
Avalanche Energy (Note 8) L = 0.1mH			E <sub>AS</sub>	18	mJ

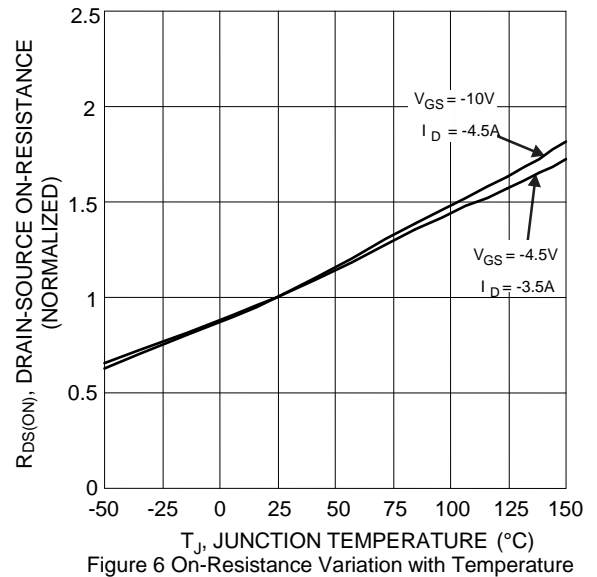
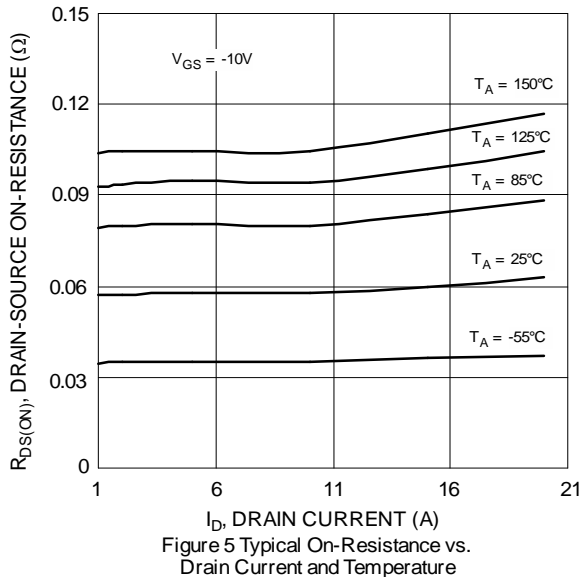
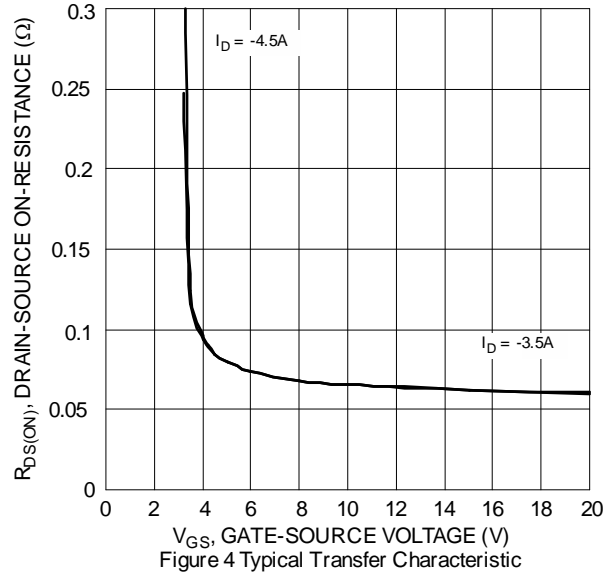
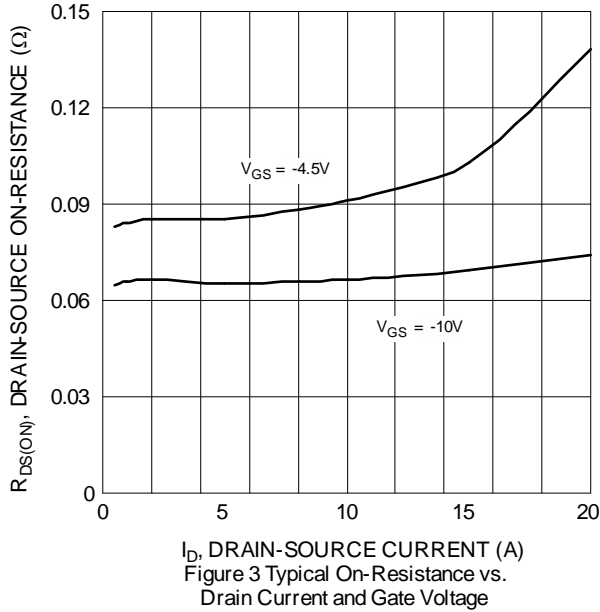
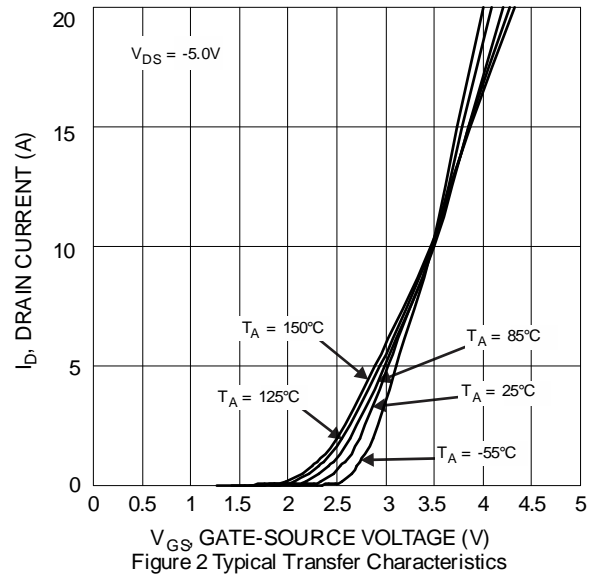
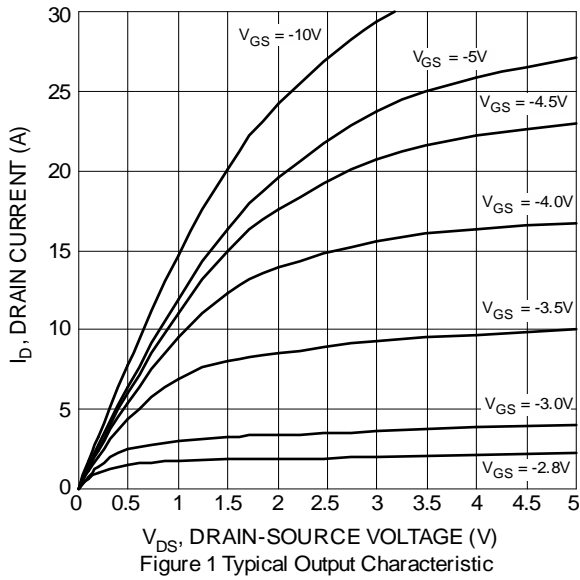
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.76	W
	T <sub>A</sub> = +70°C		0.47	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	167	°C/W
	t < 10s		121	
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.97	W
	T <sub>A</sub> = +70°C		1.30	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R <sub>θJA</sub>	64	°C/W
	t < 10s		42	
Thermal Resistance, Junction to Case (Note 7)	Steady State	R <sub>θJC</sub>	8	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -48V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	56	110	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.5A V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A
			72	130		
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>iss</sub>	—	969	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	58	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	44	—		
Gate Resistance	R <sub>g</sub>	—	14	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	8.2	—	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -12A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	17.2	—		
Gate-Source Charge	Q <sub>gs</sub>	—	3.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	3.1	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.4	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V, R <sub>GEN</sub> = 6Ω, I <sub>D</sub> = -12A
Turn-On Rise Time	t <sub>r</sub>	—	23	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	34	—		
Turn-Off Fall Time	t <sub>f</sub>	—	42	—		
Reverse Recovery Time	t <sub>RR</sub>	—	13.2	—	ns	I <sub>S</sub> = -12A, di/dt = -100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	6.2	—	nC	I <sub>S</sub> = -12A, di/dt = -100A/µs

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
  8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.



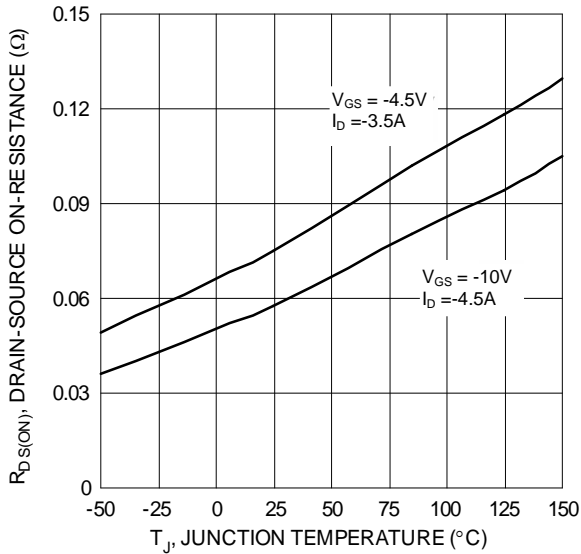


Figure 7 On-Resistance Variation with Temperature

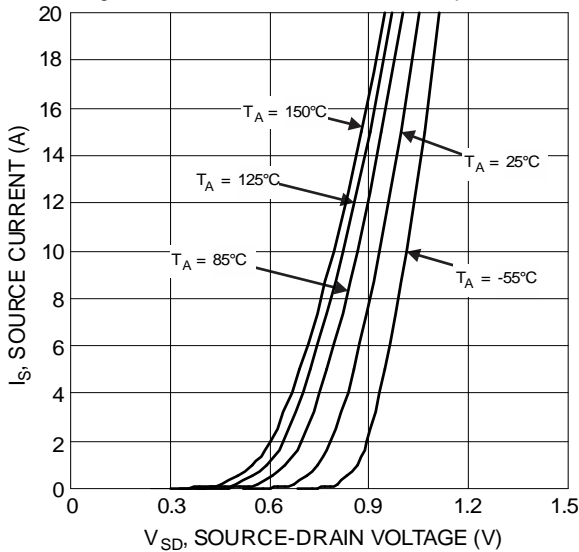


Figure 9 Diode Forward Voltage vs. Current

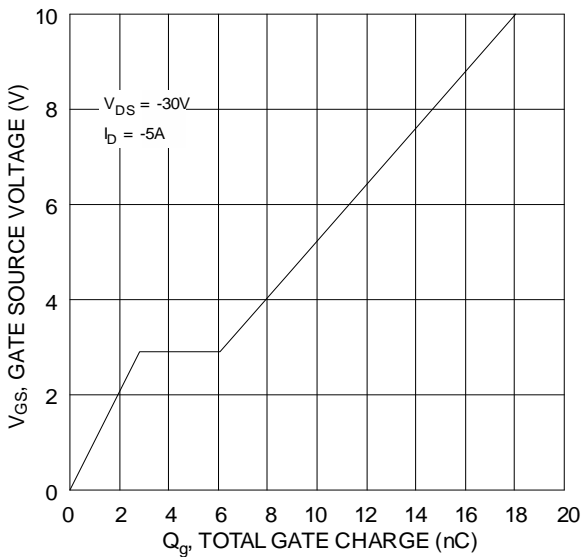


Figure 11 Gate Charge

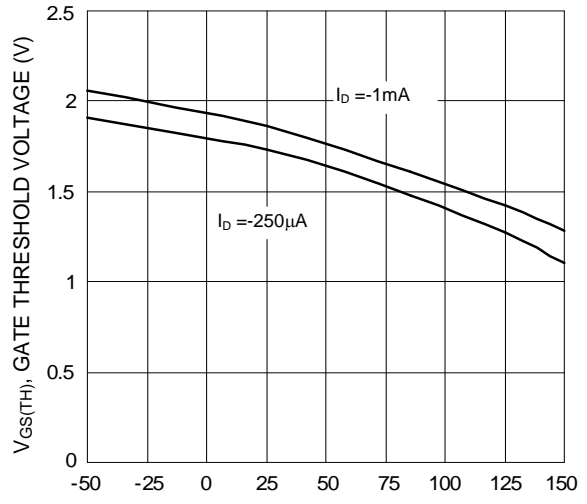


Figure 8 Gate Threshold Variation vs. Junction Temperature

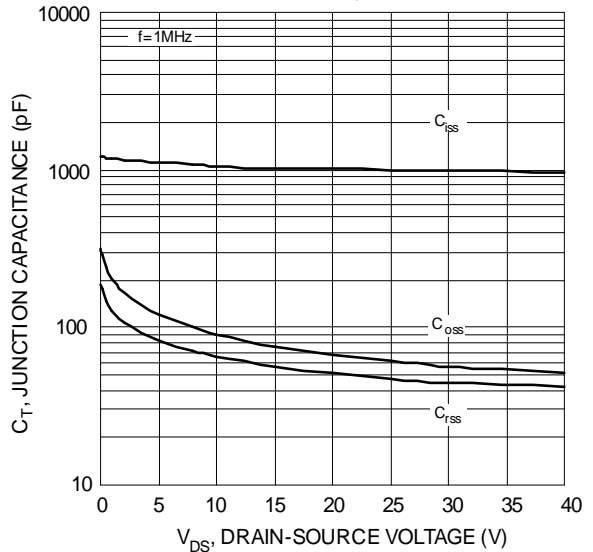


Figure 10 Typical Junction Capacitance

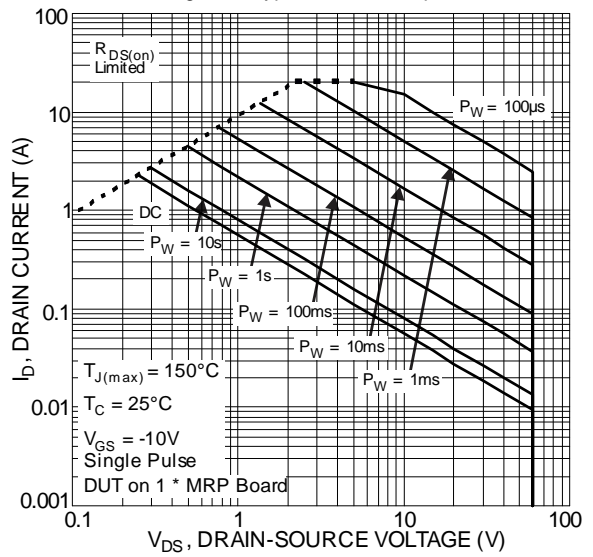
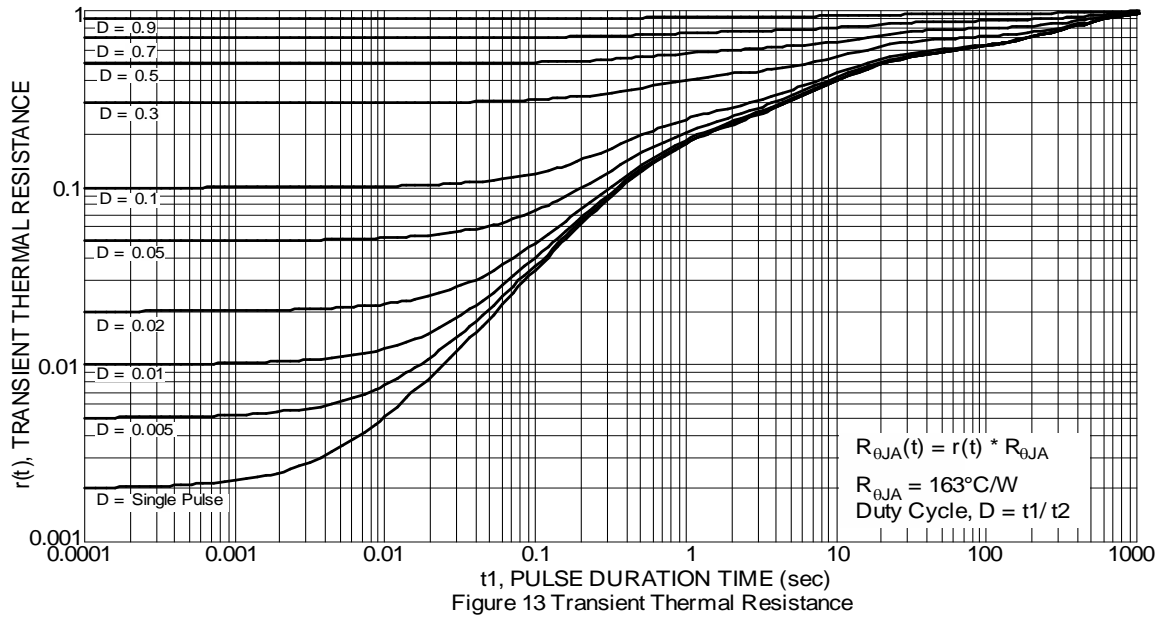


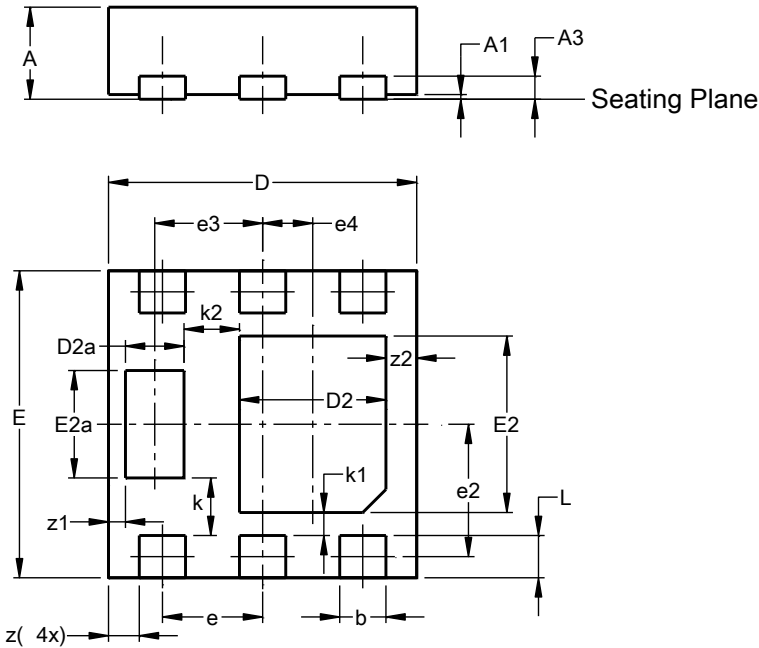
Figure 12 SOA, Safe Operation Area



**Package Outline Dimension**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**

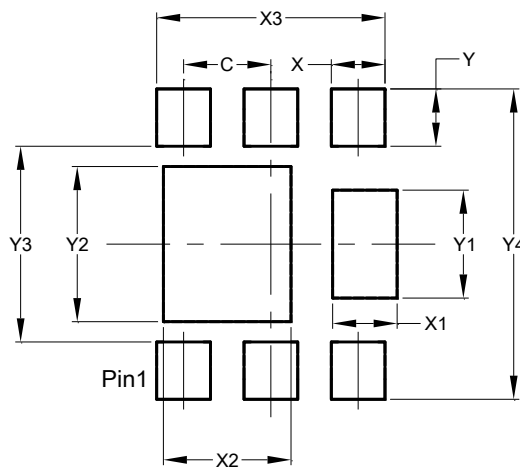


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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